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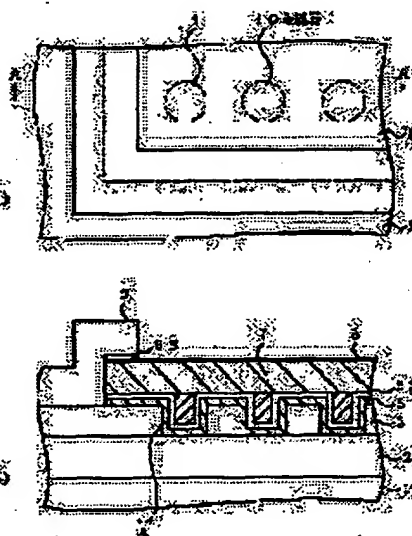
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(54) SEMICONDUCTOR DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To provide an electrode pad where aluminum is not stripped by contacting a bottom of the electrode pad to a metal layer in a groove formed on an insulation film.

SOLUTION: A semiconductor device comprises an oxidation film 3 of about 1 μm thickness which is formed on a semiconductor substrate 1, a groove 4 of 0.8 μm diameter which is formed on the oxidation film 3, Ti film 5 of about 30 nm thickness formed on the film 3 containing the groove 4, TiN film 6A of about 100 μm thickness, W film 7 imbedded in the groove 4, and electrode pad comprising Al alloy film 8 of about 600 nm thickness formed on the W film 7 and TiN film 6A. As a result, since the electrode pad is connected to a metal layer 10 formed in the groove 4 including the W film 7 and others, aluminum of the pad is not stripped even if wire bonding is achieved.



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